



2N7002DW

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C		
60V	7.5Ω @ V _{GS} = 5V	0.23A		

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- **Power Management Functions**

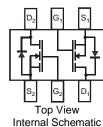
DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage .
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The 2N7002DWQ is suitable for automotive applications requiring specific change control; it is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.
- https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Ordering Information (Notes 4 and 5)

SOT363	3,000/Tape & Reel
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SOT363	10,000/Tape & Reel
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	SOT363

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

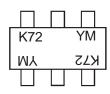
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K72 = Product Type Marking Code YM or $\overline{Y}M$ = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Duie Coue Rey															
Year	1998	1999	2000	2001	2002	2003	2004		2017	2018	2019	2020	2021	2022	2023
Code	J	K	L	М	Ν	Р	R		E	F	G	Н		J	K
-															
Month	Jan	Fe	b I	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		Ν	D

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Top View



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V	
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$		V _{DGR}	60	V	
Gate-Source Voltage		Continuous	V _{GSS}	±20	V
Gale-Source vollage	Pulsed		V _{GSS}	±40	V
Continuous Drain Current (Note 7) $V_{GS} = 5V$ Steady $T_A = +70^{\circ}C$		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_A = +100^{\circ}C$	ID	0.23 0.18 0.14	A
Maximum Continuous Body Diode Forward Current	t (Note 7)	I _S	0.53	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6)	I _{DM}	0.8	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
	$T_A = +25^{\circ}C$		0.31	
Total Power Dissipation (Note 6)	T _A = +70°C	PD	0.2	W
	T _A = +100°C		0.12	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ ext{ heta}}JA$	410	°C/W
	T _A = +25°C		0.4	
Total Power Dissipation (Note 7)	T _A = +70°C	A = +70°C PD	0.25	W
	T _A = +100°C		0.15	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{ ext{ heta}JA}$	318	°C/W
Thermal Resistance, Junction to Case (Note 7)	Steady State	$R_{\theta JC}$	135	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

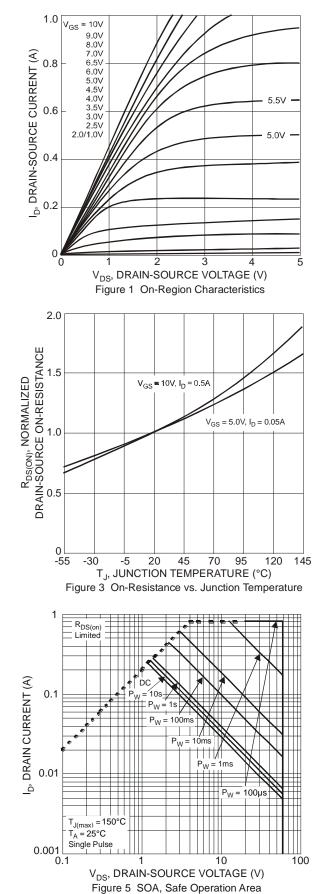
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)				71			
Drain-Source Breakdown Voltage		BV _{DSS}	60	70		V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1.0 500	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Body Leakage		I _{GSS}	_	—	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage		V _{GS(TH)}	1.0		2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C @ T _J = +125°C	R _{DS(ON)}		3.2 4.4	7.5 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0		А	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		G FS	80			mS	V _{DS} =10V, I _D = 0.2A
Diode Forward Voltage		V _{SD}		0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance		Ciss	_	22	50	pF	
Output Capacitance				11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance		Crss	_	2.0	5.0	pF	1 = 1.00012
SWITCHING CHARACTERISTICS (Note 9)							
Turn-On Delay Time		t _{D(ON)}		7.0	20		$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		t _{D(OFF)}	_	11.0	20	ns	$\label{eq:RL} \begin{split} R_L &= 150\Omega, \ V_{GEN} = 10V, \\ R_{GEN} &= 25\Omega \end{split}$

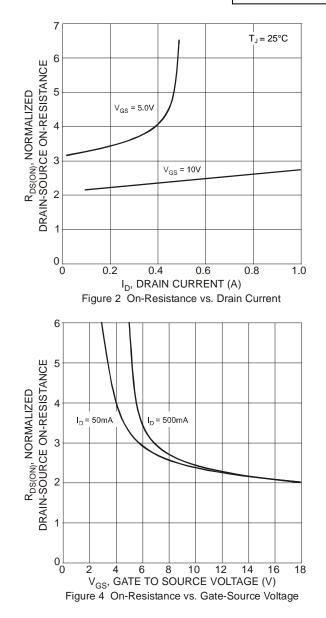
Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.







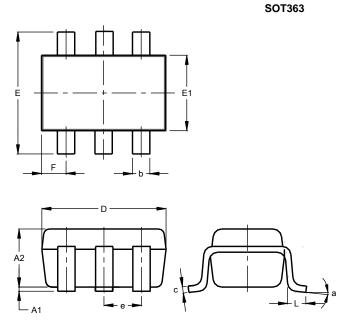




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Package Outline Dimensions

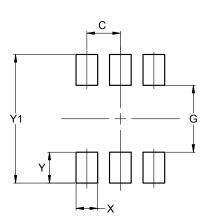
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363								
Dim	Min Max Typ							
A1	0.00	0.10	0.05					
A2	0.90 1.00 1.00							
b	0.10	0.30	0.25					
C	0.10	0.22	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	0).650 E	SC					
F	0.40	0.45	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	Dimen	sions	in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT363

Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500

0.07



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